WHAT IS CLAIMED IS:

1. A processing method for a substrate comprising:

a step of forming a protecting film on a substrate;

a step of etching a surface of said protecting film;

a step of forming an etching-resistant film on the thus etched protecting film;

a step of forming opening patterns in said protecting film and said etching-resistant film;

a step of forming an opening in said substrate by etching said substrate through said opening patterns;

a step of removing a projected end portion of said protecting film which is projected into said opening and which is produced in said opening forming step; and

a step of removing said etching-resistant film.

2. A method of manufacturing a substrate for an ink jet recording head, wherein said substrate has a supply port, penetrating said substrate, for supplying liquid and an energy generating element for generating energy for ejecting the liquid, said method comprising:

a step of forming a protecting film on a surface of said substrate which is opposite from a surface on which said energy generating element is disposed;

a step of etching a surface of said protecting film;

a step of forming an etching-resistant film on the thus etched protecting film;

a step of forming opening patterns in said protecting film and said etching-resistant film;

a step of forming an opening as said supply port in said substrate by etching said substrate through said opening patterns;

a step of removing a projected end portion of said protecting film which is projected into said opening and which is produced in said opening forming step; and

a step of removing said etching-resistant film.

3. A method according to Claim 2, wherein said substrate comprises silicon.

4. A method according to Claim 3, wherein said supply port forming step uses crystal anisotropic etching.

5. A method according to Claim 2, wherein said projected end removing step uses etching.

6. A method according to Claim 2, wherein said protecting film comprises silicon oxide.

7. A method according to Claim 2, wherein said etching-resistant film comprises polyetheramide.